

on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

14. (Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure, the electrode structure including a conductive film formed on a base substrate through an insulation film, the insulation film comprising a first film of polyimide having a plurality of openings a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.

15. (Amended) A semiconductor light-emitting device according to claim 13, further comprising a high resistance layer formed on a side of the waveguide; and said electrode structure formed on the high resistance layer.

AMENDMENT UNDER 37 CFR §1.111  
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*B' cond.* 16. (Amended) A semiconductor light-emitting device according to claim 14, further comprising *R*  
a high resistance layer formed on a side of the waveguide; and  
said electrode structure formed on the high resistance layer.

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